

FDP2710 N-Channel PowerTrench[®] MOSFET 250 V, 50 A, 42.5 mΩ

Features

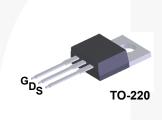
- $R_{DS(on)}$ = 36.3 m Ω (Typ.)@ V_{GS} = 10 V, I_D = 25 A
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench technology for Extremely Low $R_{\text{DS}(\text{on})}$
- High Power and Current Handing Capability
- RoHS Compliant

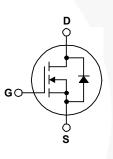
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Consumer Appliances
- Synchronous Rectification





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

| Symbol | | Parameter | | FDP2710 | Unit |
|----------------------------------|---|-----------|-------------------------|--------------|------|
| V _{DS} | Drain-Source Voltage | | rain-Source Voltage 250 | | V |
| V _{GS} | Gate-Source voltage | | ± 30 | V | |
| I _D | Drain Current - Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$) | | 50 31.3 | A A | |
| I _{DM} | Drain Current | - Pulsed | (Note 1) | See Figure 9 | A |
| E _{AS} | Single Pulsed Avalanche Energy (Note 2) | | (Note 2) | 145 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (No | | (Note 3) | 4.5 | V/ns |
| P _D | Power Dissipation (T _C = 25°C) - Derate above 25°C | | 260 2.1 | W W/°C | |
| T _{J,} T _{STG} | Operating and Storage Temperature Range | | | -55 to +150 | °C |
| Τ _L | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds | | | 300 | °C |

Thermal Characteristics

| Symbol | Parameter | FDP2710 | Unit |
|---------------------|---|---------|------|
| $R_{	ext{	heta}JC}$ | Thermal Resistance, Junction-to-Case, Max. | 0.48 | °C/W |
| R_{\thetaJA} | Thermal Resistance, Junction-to-Ambient, Max. | 62.5 | °C/W |

www.fairchildsemi.com

October 2013

| Device Marking | | Device | ce Package Reel Size 1 | | Тар | Tape Width | | Quantity | | |
|--|--|-----------------------------|--------------------------|---|---------------------------------------|------------|----------|-----------|----------|----|
| | | TO | D-220 Tube | | N/A | | 50 units | | | |
| Electrica | l Chai | racteristics T _c | _C = 25°C unle | ess otherwis | e noted | | | | | |
| Symbol | | Parameter | | Conditions | | Min | Тур | Max | Unit | |
| Off Characte | eristics | | | | | | | | | |
| BV _{DSS} [| Drain-Sou | urce Breakdown Volta | ige | $V_{GS} = 0V, I_D = 250\mu A, T_J = 25^{\circ}C$ | | 250 | | | V | |
| 000 | BVDSS Breakdown Voltage Temperature | | | I _D = 250μA, Referenced to 25°C | | | 0.25 | | V/∘C | |
| I _{DSS} Z | Zero Gate Voltage Drain Current | | nt | $V_{DS} = 250V, V_{GS} = 0V$ $V_{DS} = 250V, V_{GS} = 0V, T_{C} = 125^{\circ}C$ | | | | 10 500 | μΑ μΑ | |
| I _{GSSF} (| Gate-Bod | y Leakage Current, F | orward | V _{GS} = 30\ | /, V _{DS} = 0V | | | | 100 | nA |
| I _{GSSR} (| Gate-Bod | y Leakage Current, R | Reverse | $V_{GS} = -30V, V_{DS} = 0V$ | | | | -100 | nA | |
| On Characte | ristics | | | | | | | | | |
| V _{GS(th)} (| Gate Threshold Voltage | | | V _{DS} = V _{GS} | _s , I _D = 250μA | | 3.0 | 4.0 | 5.0 | V |
| R _{DS(on)} S | Static Drain-Source On-Resistance | | ance | V _{GS} = 10V, I _D = 25A | | | 36.3 | 42.5 | mΩ | |
| g _{FS} F | Forward Transconductance | | | V _{DS} = 10V | /, I _D = 25Α | | | 63 | | S |
| Dynamic Cha | aracteris | tics | | | | | | | | |
| C _{iss} I | Input Capacitance | | | | | | 5470 | 7280 | pF | |
| C _{oss} (| Output Capacitance Reverse Transfer Capacitance | | | V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz | | | 426 | 570 | pF | |
| | | | | | | | 97 | 146 | pF | |
| Switching Cl | haracteri | stics | | | | | | | | |
| t _{d(on)} | Turn-On Delay Time Turn-On Rise Time | | | | | | 80 | 170 | ns | |
| t _r 1 | | | | V _{DD} = 125V, I _D = 50A V _{GS} = 10V, R _{GEN} = 25Ω | | | | 252 | 515 | ns |
| t _{d(off)} | Turn-Off [| Delay Time | | | | | | 112 | 235 | ns |
| t _f 1 | Turn-Off F | all Time | | | | (Note 4) | | 154 | 320 | ns |
| Q _g 1 | Total Gate | e Charge | | $V_{DS} = 125V, I_D = 50A$ $V_{GS} = 10V$ (Note 4) | | | | 78 | 101 | nC |
| Q _{gs} (| Gate-Sou | rce Charge | | | | | | 34 | , | nC |
| Q _{gd} (| Gate-Drai | in Charge | | | | (Note 4) | / | 18 | | nC |
| Drain-Source | e Diode (| Characteristics and | Maximum | Ratings | | | | | | |
| I _S Maximum Continuous Drain-Source Dio | | | ource Diode | e Forward | Current | | | | 50 | Α |
| | Maximum Pulsed Drain-Source Diode F | | e Diode Foi | orward Current | | | | 150 | Α | |
| V _{SD} [| Drain-Sou | urce Diode Forward V | oltage | V _{GS} = 0V, I _S = 50A | | | | 1.2 | V | |
| t _{rr} F | Reverse I | Recovery Time | | V _{GS} = 0V, | | | | 163 | | ns |
| | Reverse I | Recovery Charge | | $dI_F/dt = 100A/\mu s$ | | | | 1.3 | | μC |

Notes:

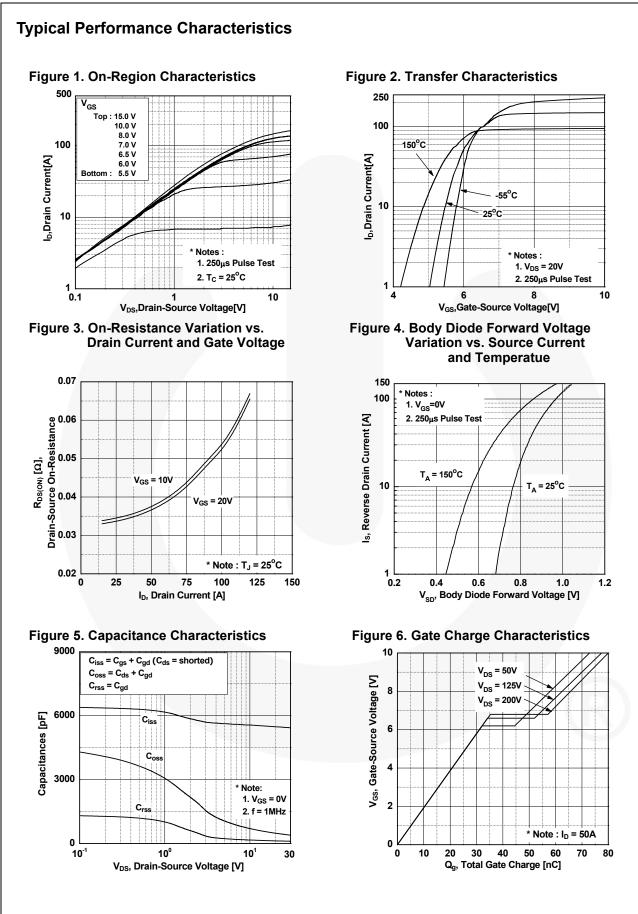
1. Repetitive Rating: Pulse width limited by maximum junction temperature

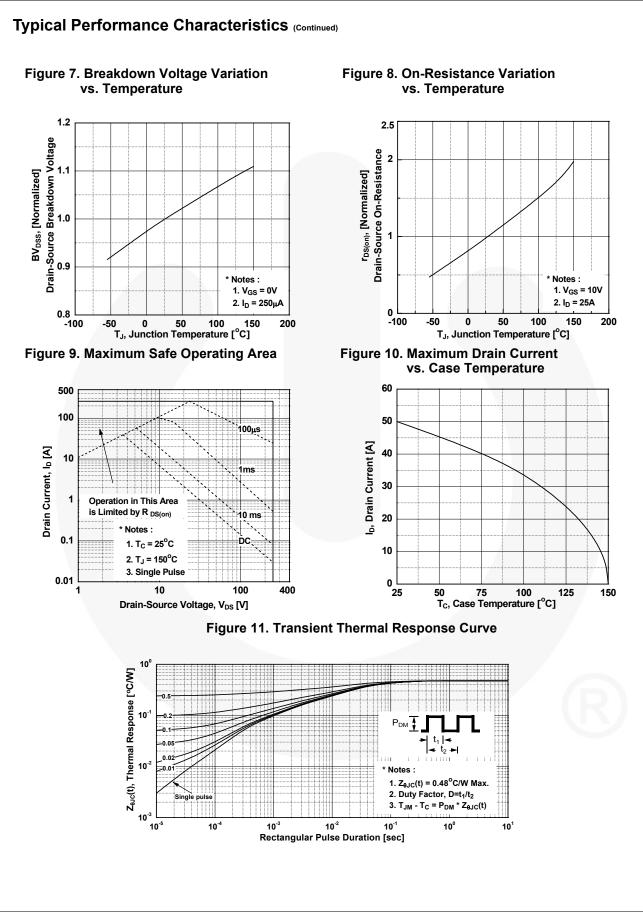
Package Marking and Ordering Information

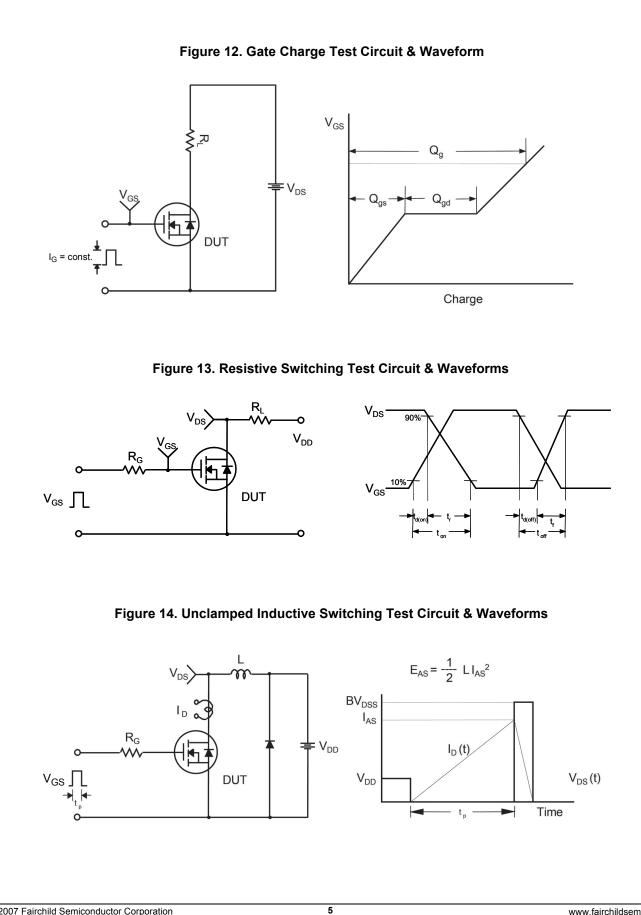
2. L = 1mH, I_{AS} = 17A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25°C

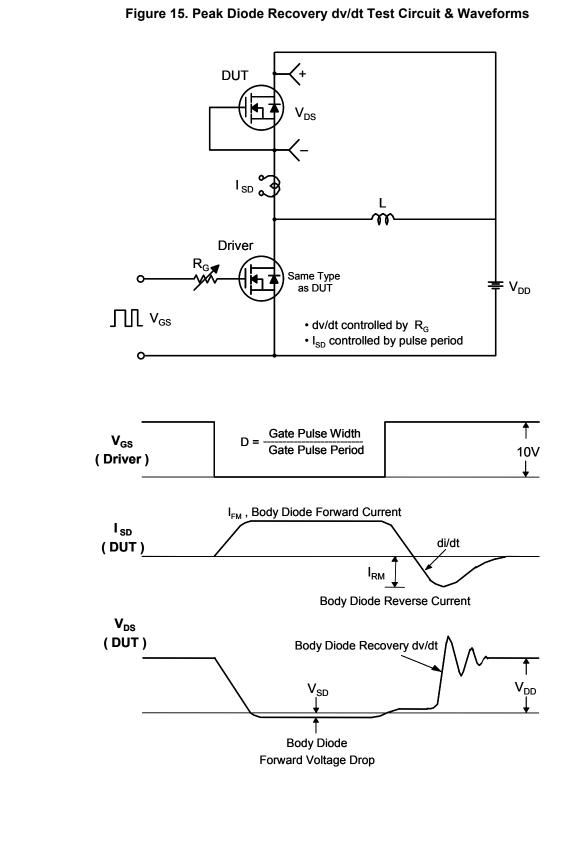
3. $I_{SD} \leq$ 50A, di/dt \leq 100A/µs, $V_{DD} \leq$ BV_{DSS}, Starting T_J = 25°C

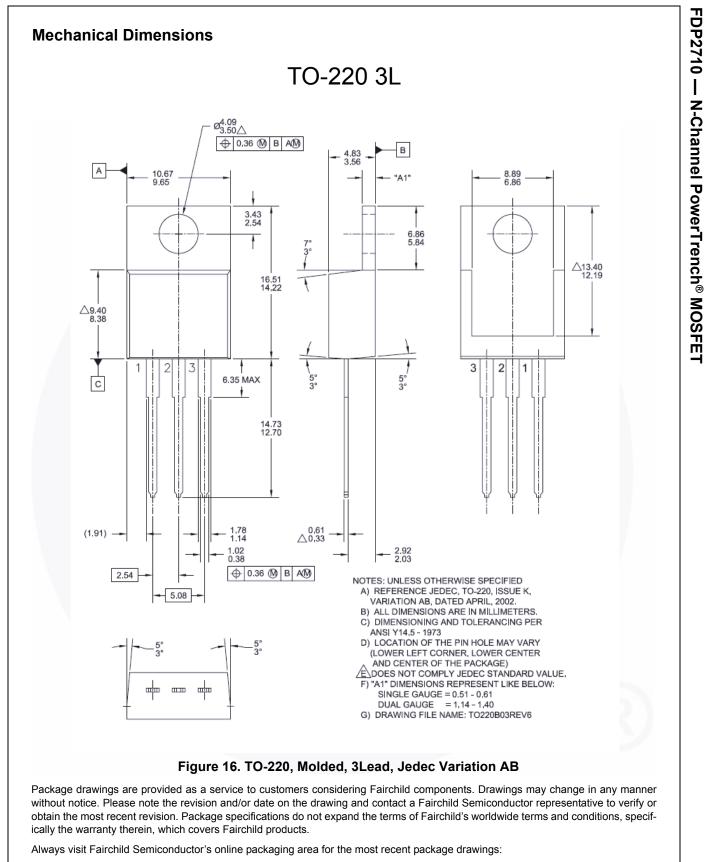
4. Essentially Independent of Operating Temperature Typical Characteristics











http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT220-003

Dimension in Millimeters



SEMICONDUCTOR

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

| AccuPower™ | F-PFS™ | R | Sync-Lock™ |
|--------------------------------------|-------------------------------------|---------------------------------------|-------------------------------------|
| AX-CAP [®] * | FRFET® | | SYSTEM ®* |
| BitSiC™ | Global Power Resource SM | PowerTrench [®] | GENERAL |
| Build it Now™ | GreenBridge™ | PowerXS™ | TinyBoost [®] |
| CorePLUS™ | Green FPS™ | Programmable Active Droop™ | TinyBuck [®] |
| CorePOWER™ | Green FPS™ e-Series™ | QFET® | TinyCalc™ |
| CROSSVOLT™ | G <i>max</i> ™ | QS™ | |
| CTL™ | GTO™ | Quiet Series™ | TinyLogic [®] TINYOPTO™ |
| Current Transfer Logic™ | IntelliMAX™ | RapidConfigure™ | TinyPower™ |
| DEUXPEED® | ISOPLANAR™ | [™] | |
| Dual Cool™ | Marking Small Speakers Sound Loude | r 🔾 | TinyPWM™ |
| EcoSPARK [®] | and Better™ | Saving our world, 1mW/W/kW at a time™ | TinyWire™ Trans CiO™ |
| EfficentMax™ | MegaBuck™ | SignalWise™ | TranSiC™ |
| ESBC™ | MIČROCOUPLER™ | SmartMax™ | TriFault Detect™ |
| | MicroFET™ | SMART START™ | TRUECURRENT®* |
| | MicroPak™ | Solutions for Your Success™ | µSerDes™ |
| Fairchild [®] | MicroPak2™ | SPM® | \mathcal{M} |
| Fairchild Semiconductor [®] | MillerDrive ™ | STEALTH™ | <mark>∕ Ser</mark> Des" |
| FACT Quiet Series™ | MotionMax™ | SuperFET® | UHC [®] |
| FACT Quiet Series | mWSaver® | SuperSOT™-3 | Ultra FRFET™ |
| FACT® | OptoHiT™ | SuperSOT™-6 | UniFET™ |
| FAST® | OPTOLOGIC® | SuperSOT™-8 | VCX™ |
| FastvCore™ | OPTOPLANAR [®] | SupreMOS [®] | VisualMax™ |
| FETBench™ | OF TOT EANAR | SyncFET™ | VoltagePlus™ |
| FPS™ | | Synci Li m | XS™ |
| | | | |
| | | | |

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Term

| Datasheet Identification | Product Status | Definition |
|--------------------------|-----------------------|---|
| Advance Information | Formative / In Design | Datasheet contains the design specifications for product development. Specifications may change in any manner without notice. |
| Preliminary | First Production | Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design. |
| No Identification Needed | Full Production | Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design. |
| Obsolete | Not In Production | Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only. |

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor: <u>FDP2710</u>